



HT 2815

BOX AF

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Kiyoshi IRINO**

Serial No.: 09/428,052

Filed: October 27, 1999

Group Art Unit: 2815

Examiner: J. Diaz

For: **METHOD OF FABRICATING A SEMICONDUCTOR DEVICE CONTAINING NITROGEN IN A GATE OXIDE FILM (AS AMENDED)**

**AMENDMENT AFTER FINAL REJECTION**

**BOX AF**

Commissioner for Patents  
Washington, D.C. 20231

Date: November 9, 2001

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Sir:

In response to the Office Action dated August 9, 2001, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please amend claims 6 and 10 as follows:

6. (Three Times Amended) A method of fabricating a semiconductor device, comprising the steps of:

forming a gate oxide film on a substrate;

forming a gate electrode pattern on said gate oxide film;

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